

A 5 Gb/s Radiation Tolerant Laser Driver in CMOS 0.13 μm technology

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Outline



Sezione di Torino

- * The GBT project
- * The GBLD laser driver
- * Modulator architecture
- * Test results
- * Conclusions

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GBT Chipset



Sezione di Torino

Radiation tolerant chipset :

- * GBTIA : Transimpedance optical receiver
- * GBLD : Laser driver
- * GBTx : Data and Timing Transceiver
- * GBT-SCA : Slow control ASIC

Target Applications :

- * Data readout
- * TTC
- * Slow control and monitoring links

Supports :

- * Bidirectional data transmission
- * Bandwidth :
 - Line rate : 4.8 Gb/s
 - Effective : 3.36 Gb/s

Radiation Tolerance :

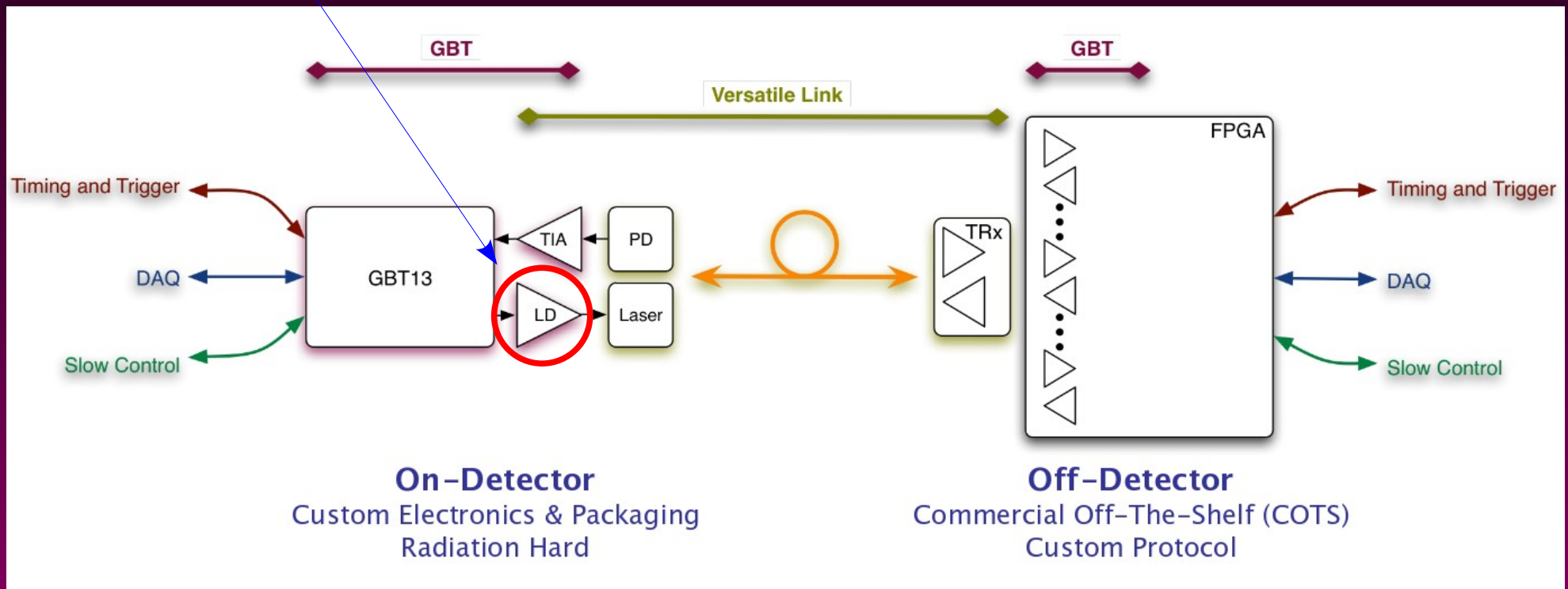
- * Total dose
- * Single Event Upset

GBT architecture



Sezione di Torino

GBLD



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GBLD specifications



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- * Max bit rate : 5 Gb/s
- * Possibility to drive both edge emitting lasers and VCSELs
- * Differential and single ended driving
- * Modulation current : $2 \div 24$ mA
- * Bias current : $2 \div 43$ mA
- * Pre-emphasis/de-emphasis current : $0 \div 12$ mA
- * Independently programmable rising and falling edge pre/de-emphasis
- * I²C digital control with SEU protection

Challenging items



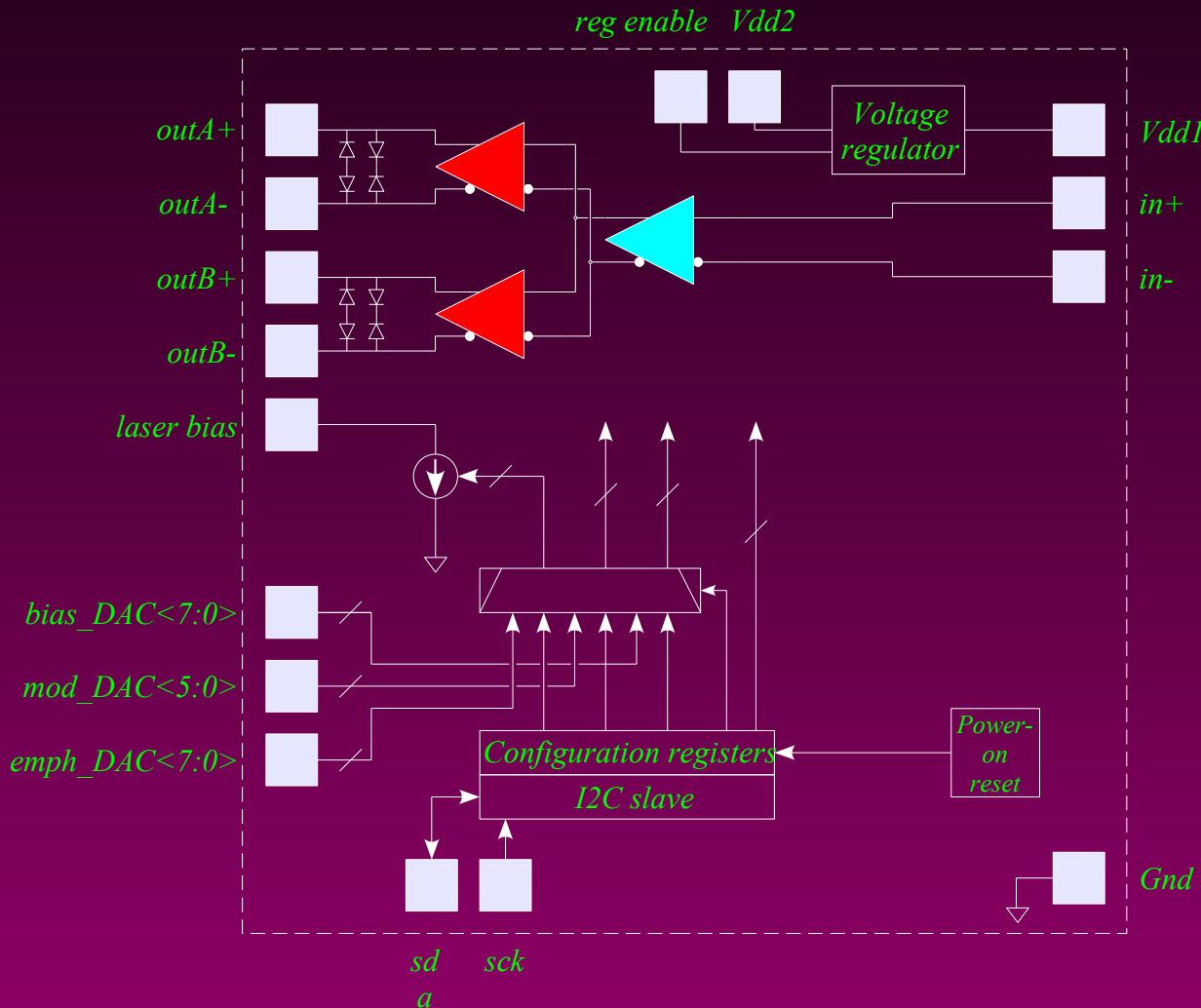
Sezione di Torino

- * EE lasers $I_{\text{ON}} \sim \text{tens of mA}$, $R_{\text{D}} \sim \Omega$
- * VCSEL $I_{\text{ON}} \sim \text{mA}$, $R_{\text{D}} \sim \text{tens of } \Omega$
- * Big devices needed to drive high currents
 - big parasitic capacitance
- * 2.5 V power supply needed for proper laser bias
- * Commercial transceivers normally :
 - are based on (SiGe) BiCMOS technology
 - address only one type of lasers

GBT block diagram



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- * Two drivers architecture
- * Same driving signal
- * Same control DAC
- * Range 1 : one driver - $2 \div 12$ mA and 50Ω termination
- * Range 2 : two drivers in parallel - $4 \div 24$ mA and 25Ω termination

Outline



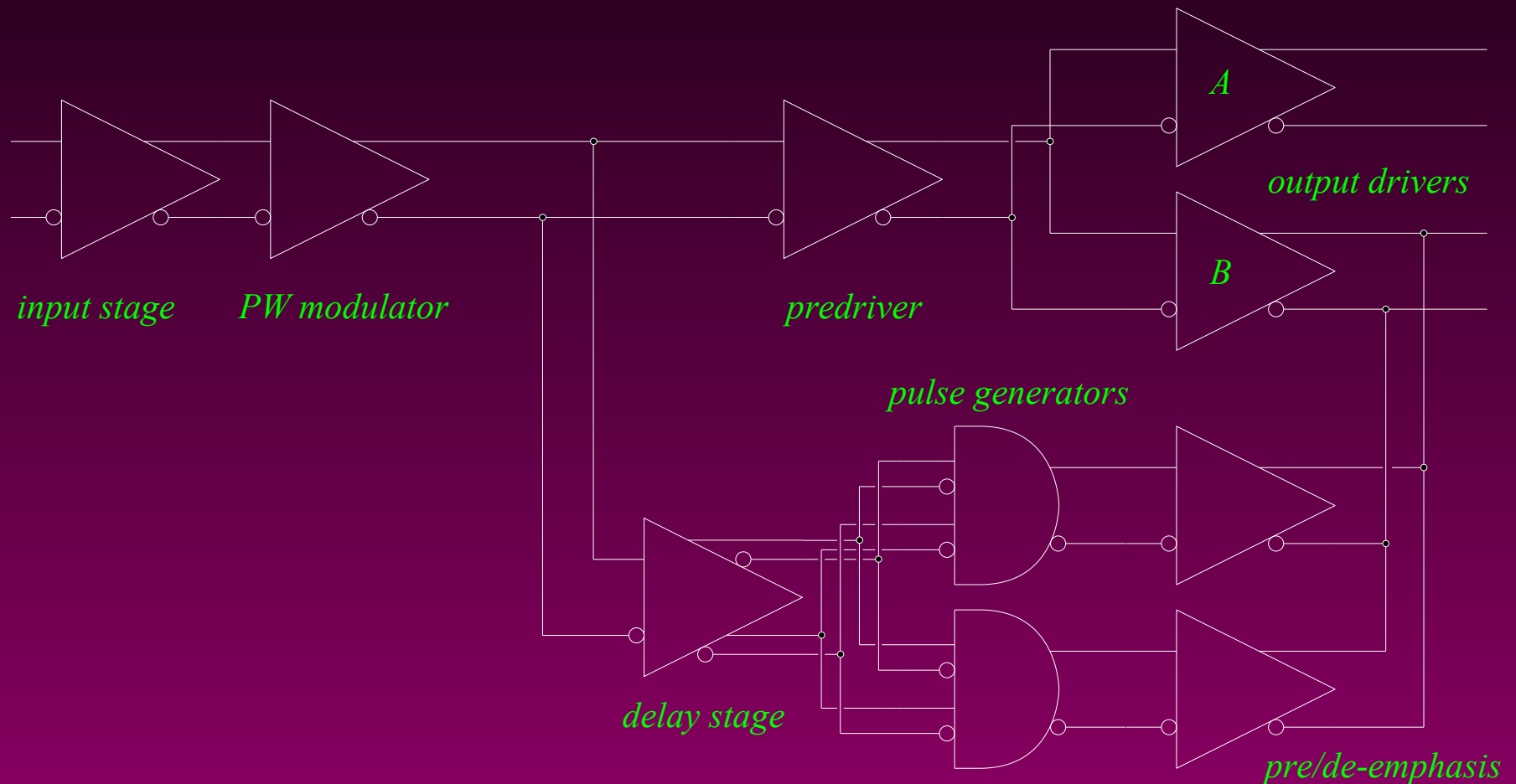
Sezione di Torino

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- **Modulator architecture**
- * Test results
- * Conclusions

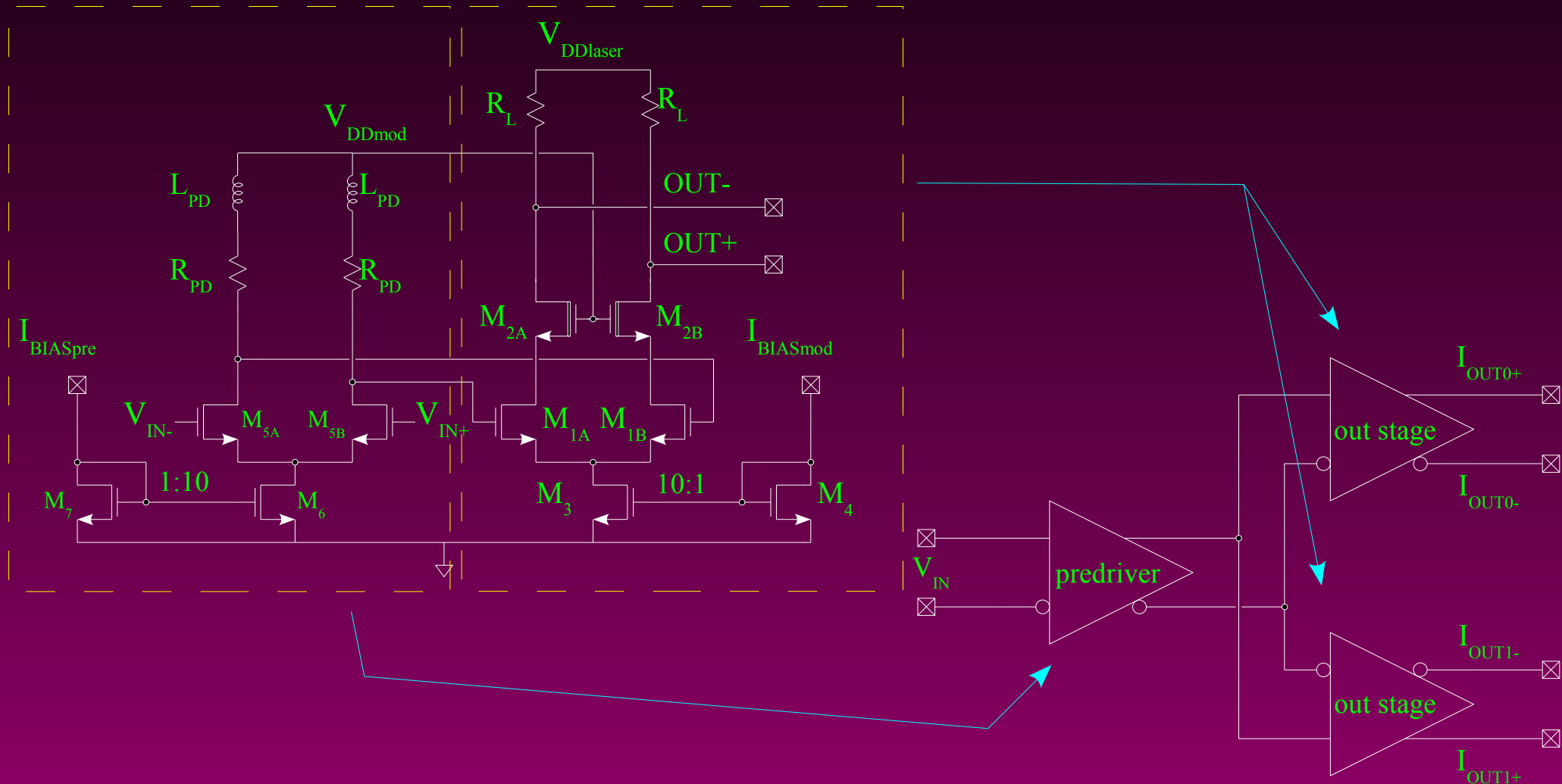
Modulator scheme



Sezione di Torino



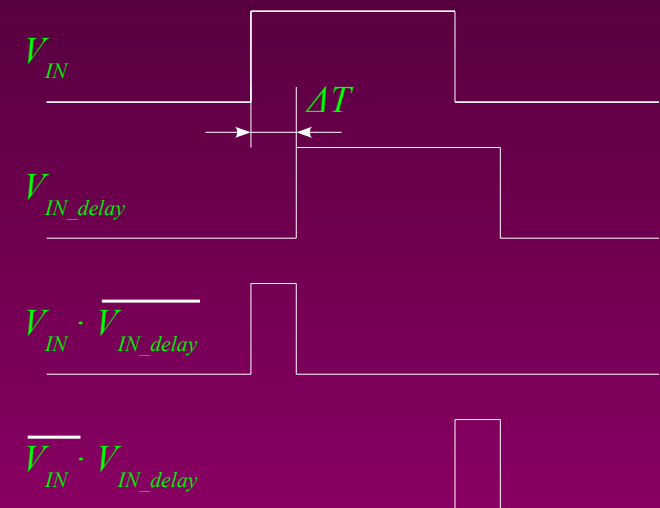
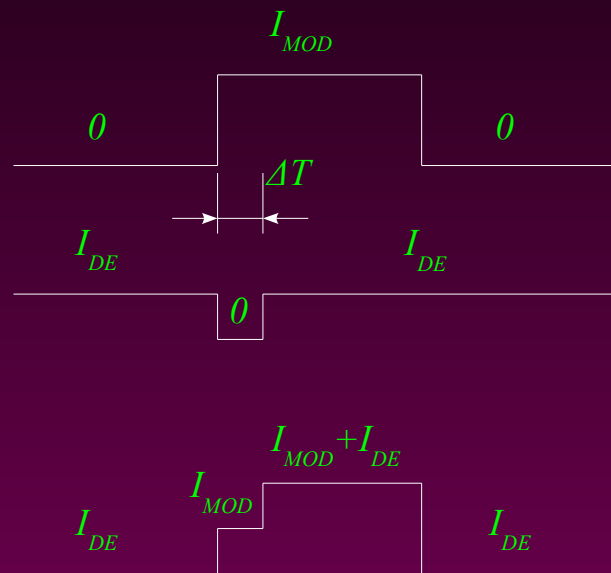
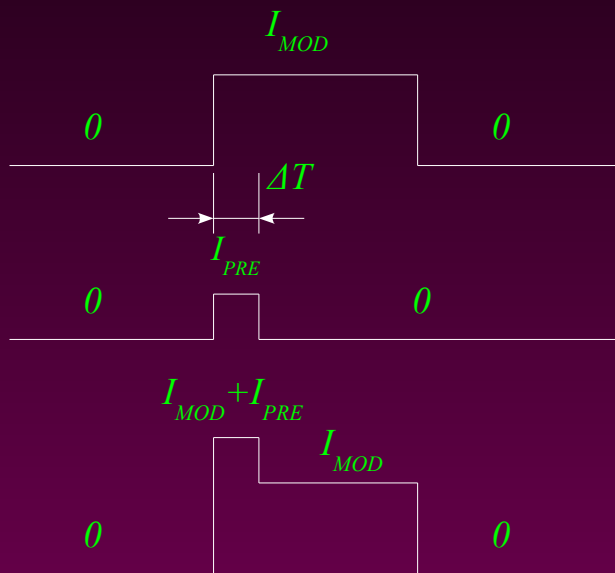
Output drivers



Pre/de-emphasis - 1



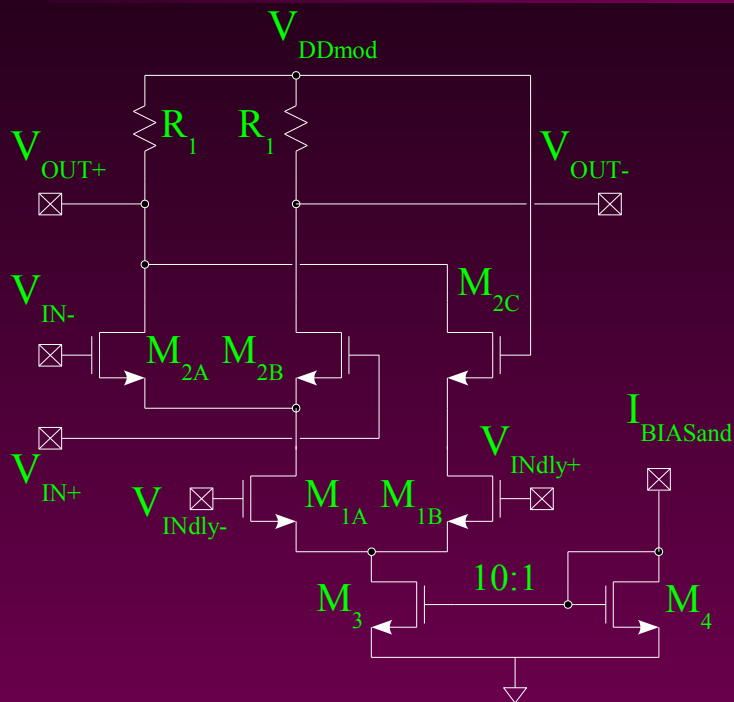
Sezione di Torino



Pre/de-emphasis - 2

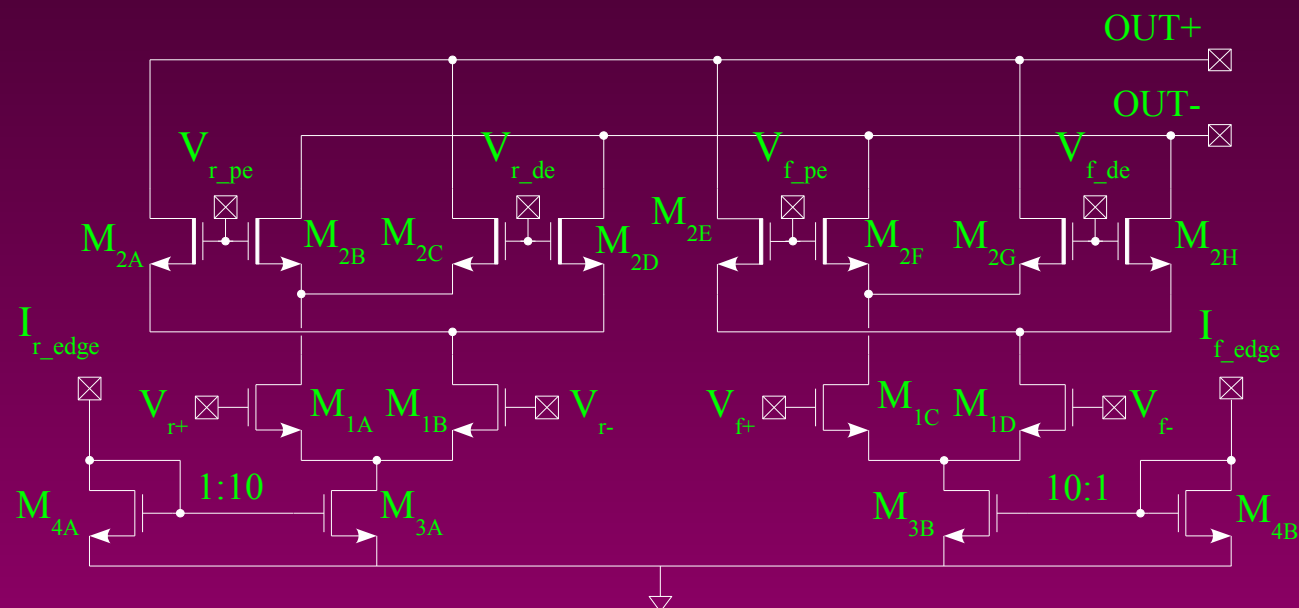


Sezione di Torino

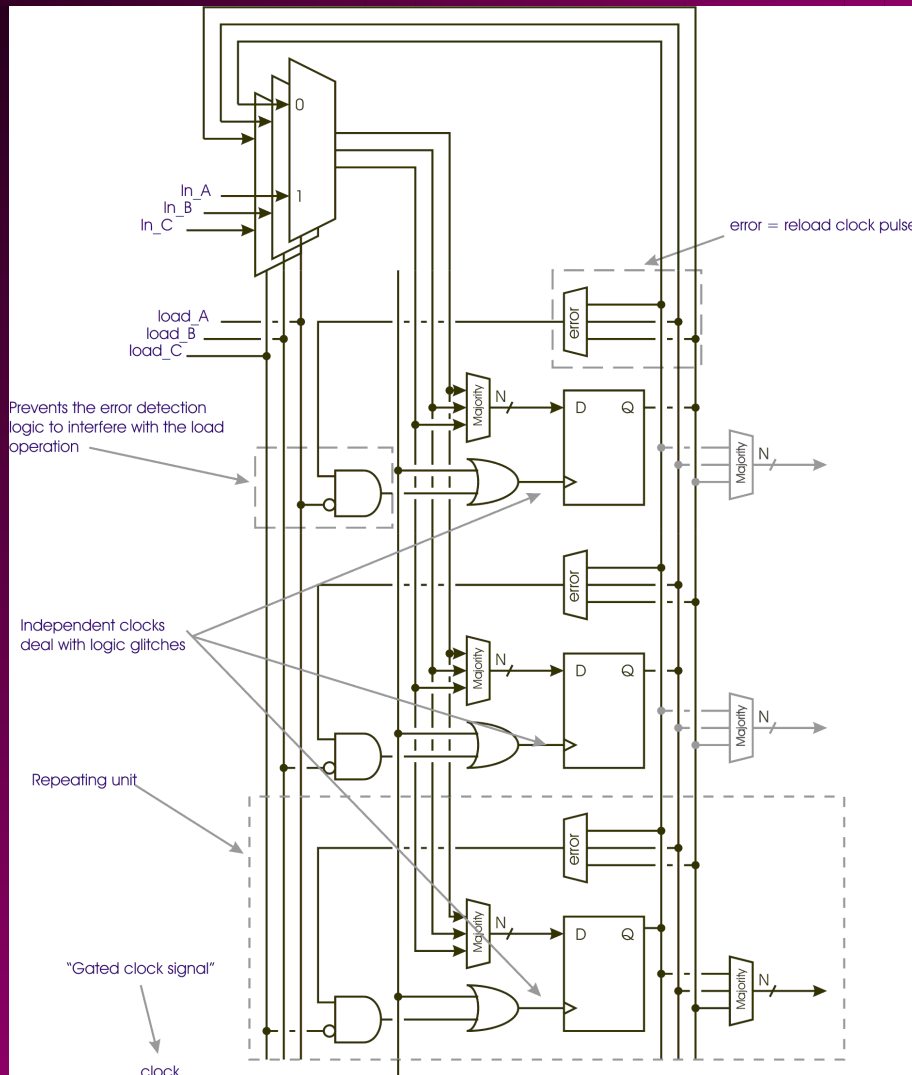


*differential
AND gate*

*Pre/de emphasis
output driver*



SEU protection

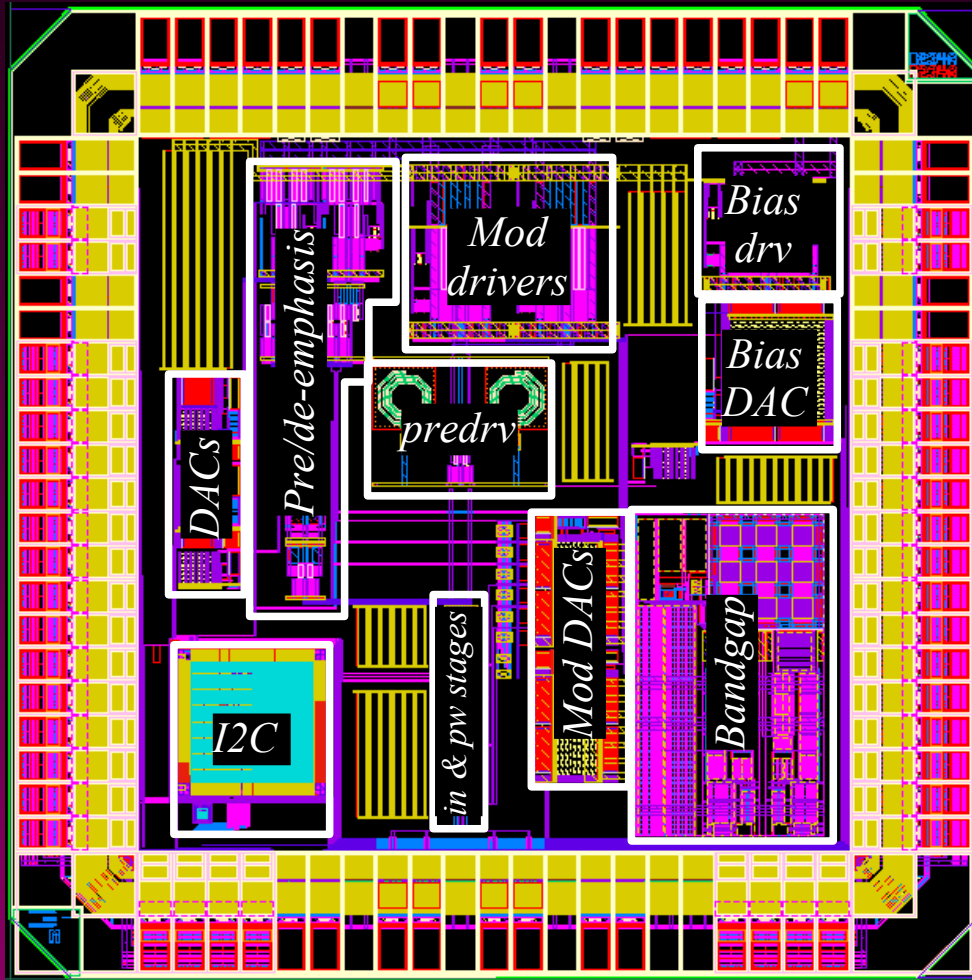


- * Triple modular redundancy with self correction
- * I²C clock is not continuous → asynchronous circuit required
- * A clock rising edge is generated when :
 - i. a corrupted bit is detected,
 - and*
 - ii. there is no load signal
- * Once the bit is corrected, the clock signal is automatically cleared

Chip layout



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- * CMOS 0.13 μm technology
- * 6+2 metal layers
- * Area : $2 \times 2 \text{ mm}^2$
- * 2 power supplies : 1.5 V and 2.5 V
- * Power consumption : max 460 mW
- * $\sim 750 \text{ pF}$ filter capacitor/supply
- * Package : QFN28 $5 \times 5 \text{ mm}^2$

Outline



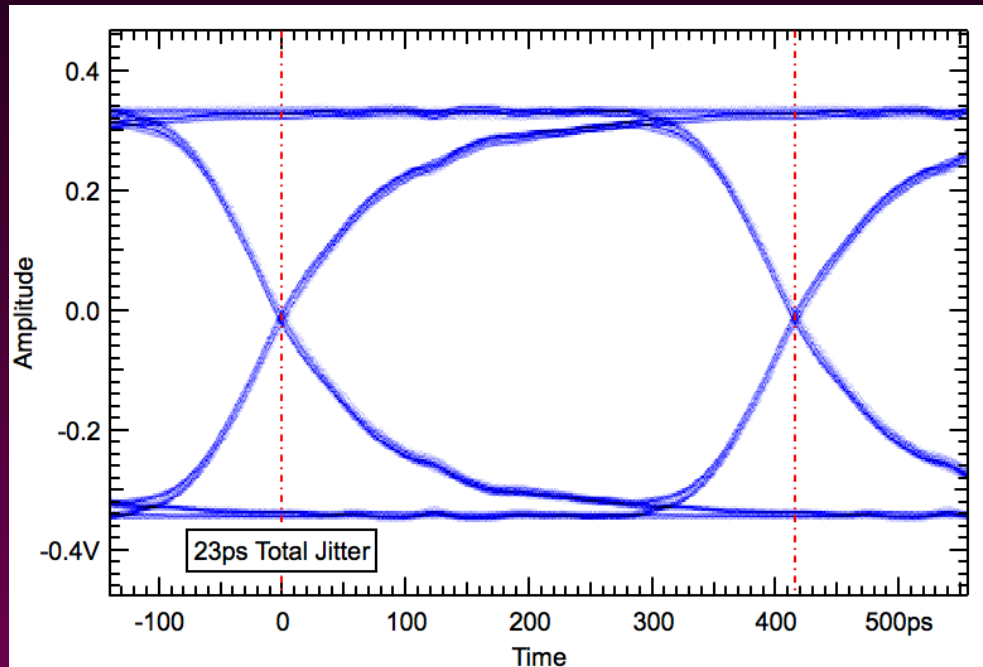
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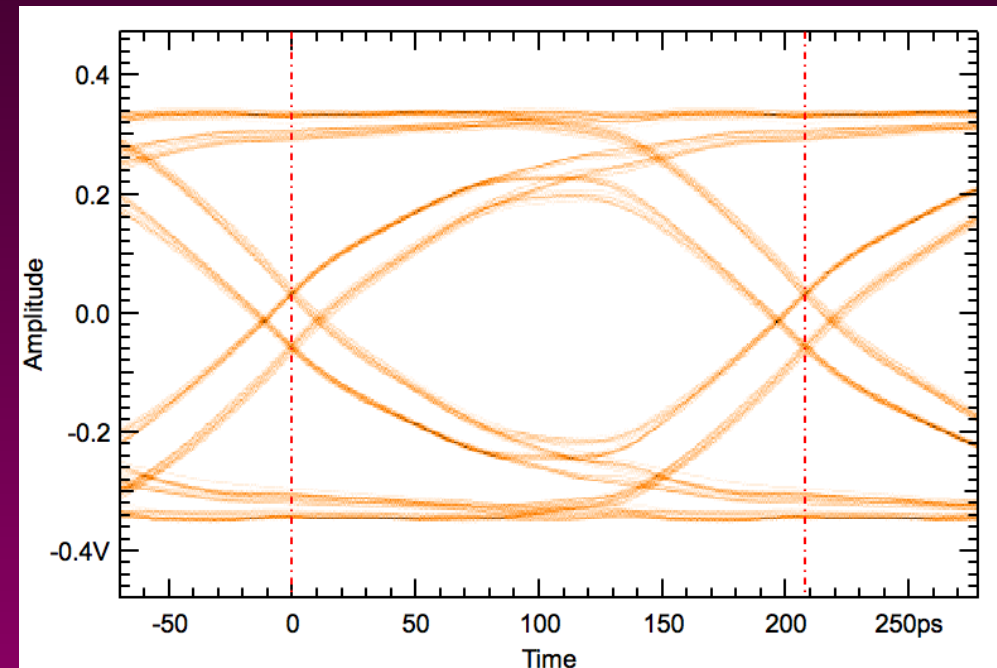
Eye diagram



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@ 2.4 Gb/s

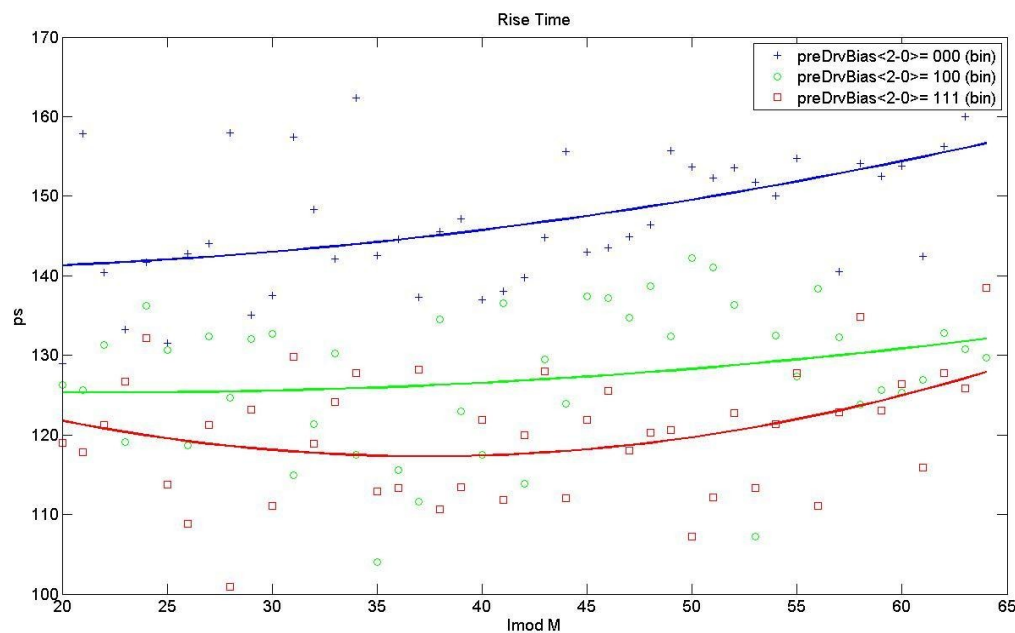


@ 4.8 Gb/s

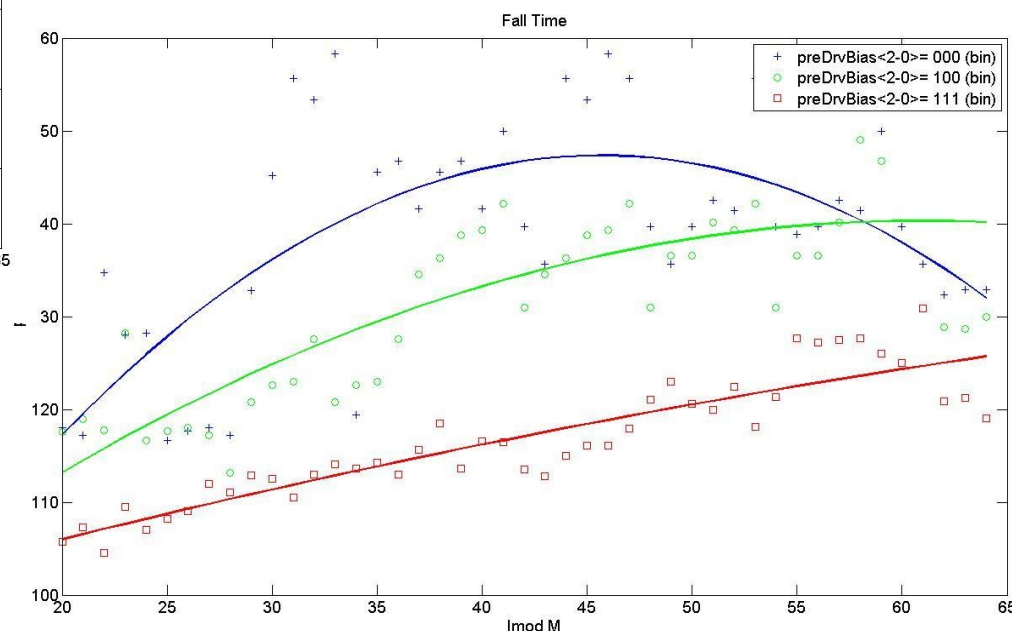
Rise/fall time



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@ 5 Gb/s

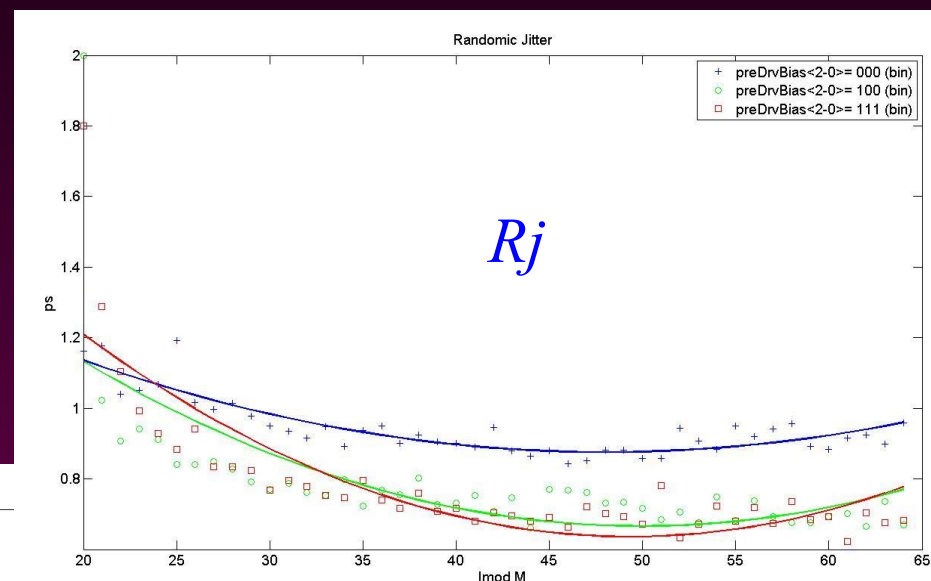
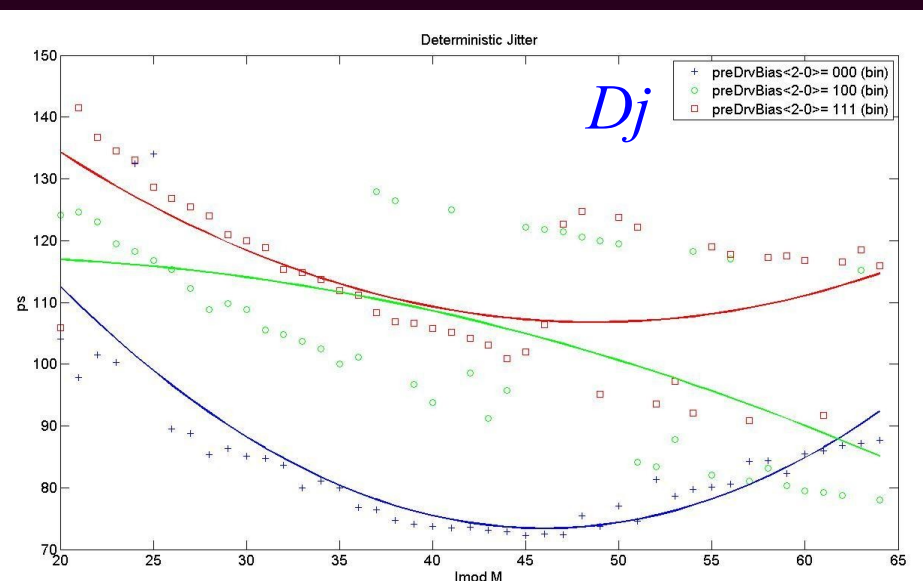


Predriver biased at :
6 mA (blue)
10 mA (green)
14 mA (red)

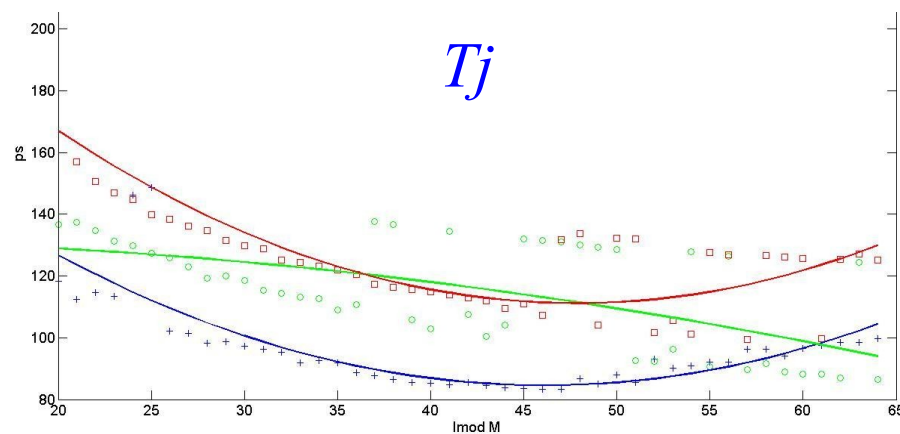
Jitter



Sezione di Torino



Total Jitter

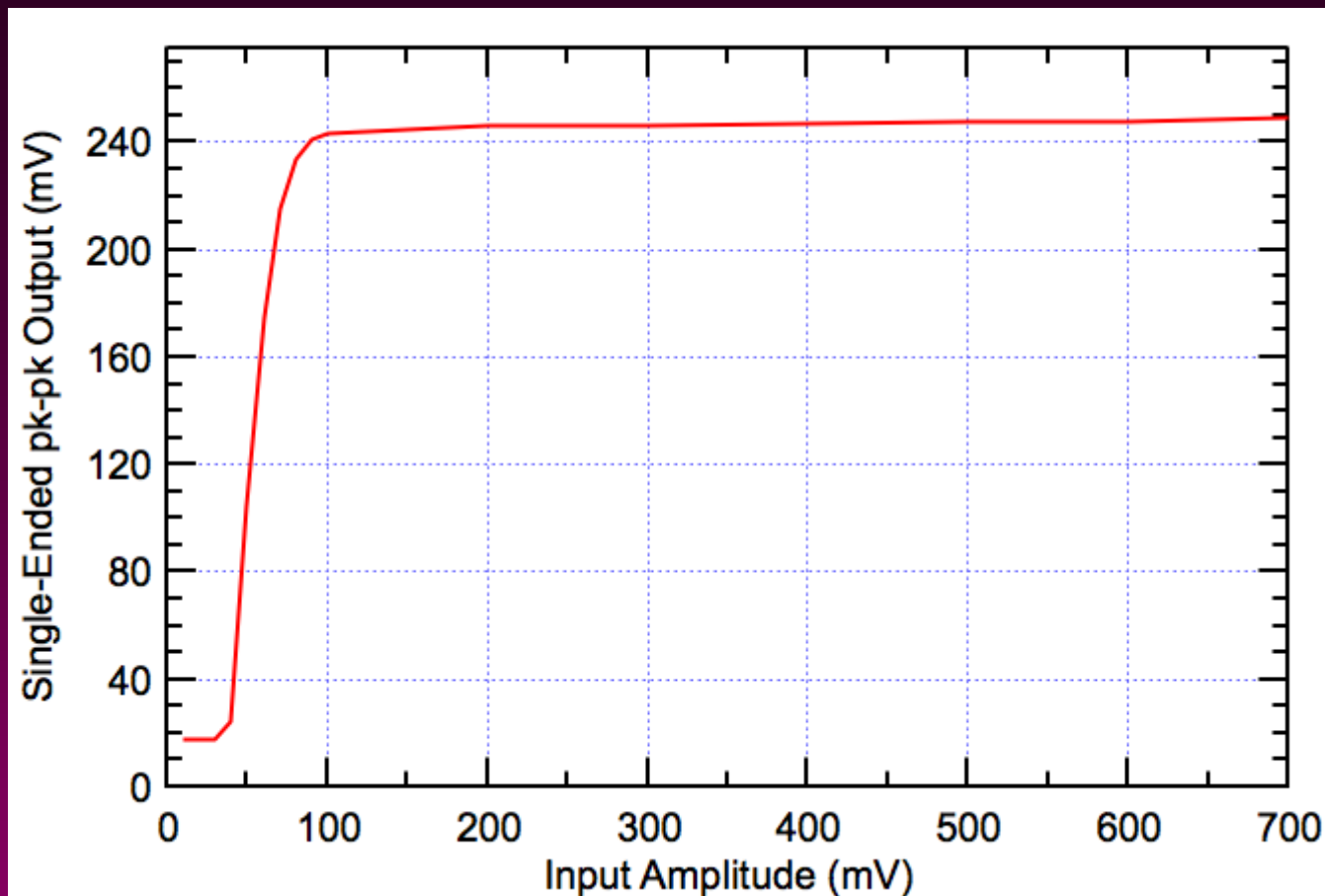


@ 5 Gb/s

Input range



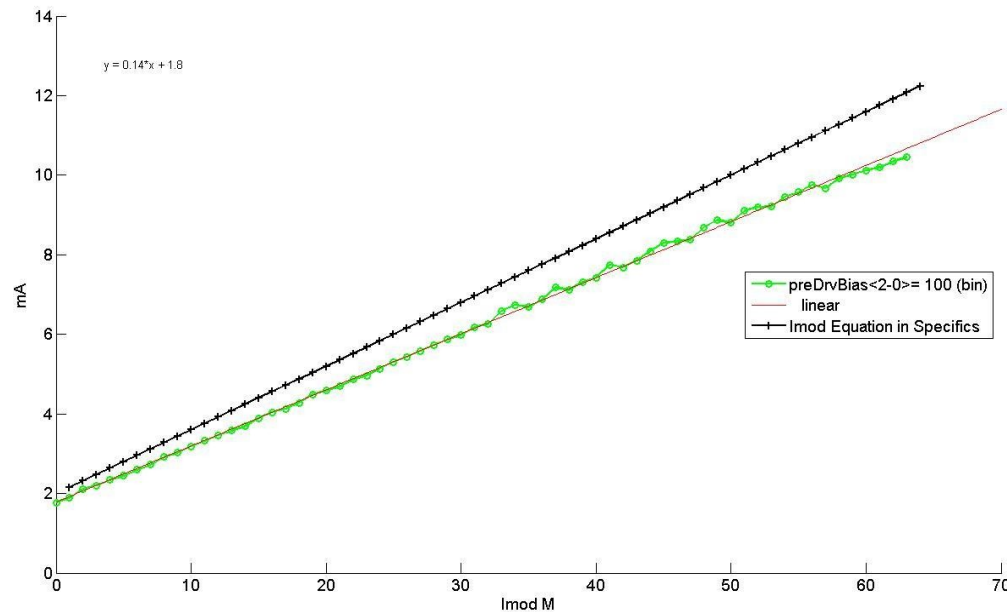
Sezione di Torino



DACs linearity

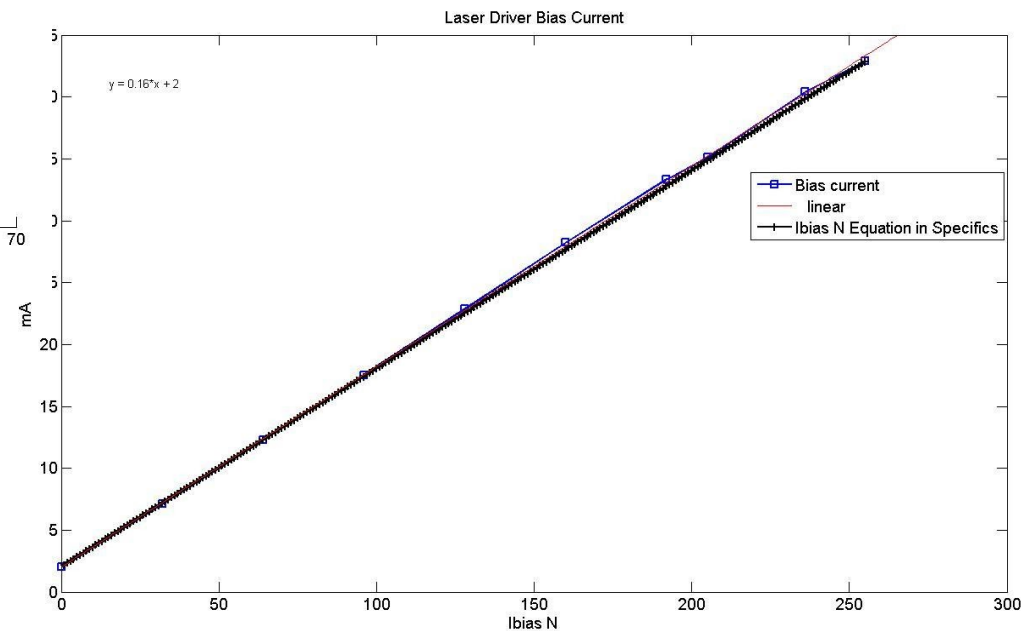


Sezione di Torino



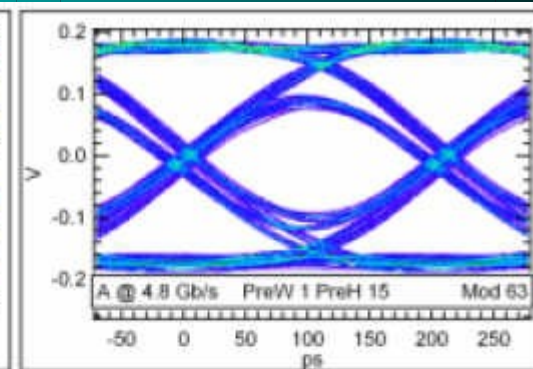
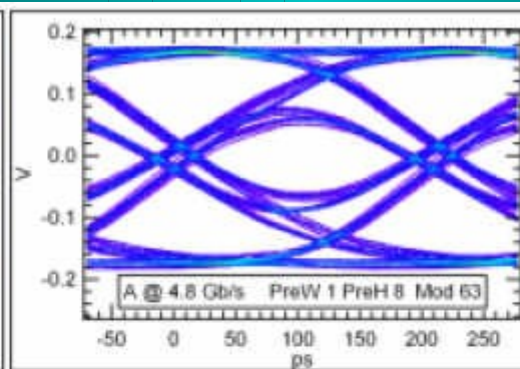
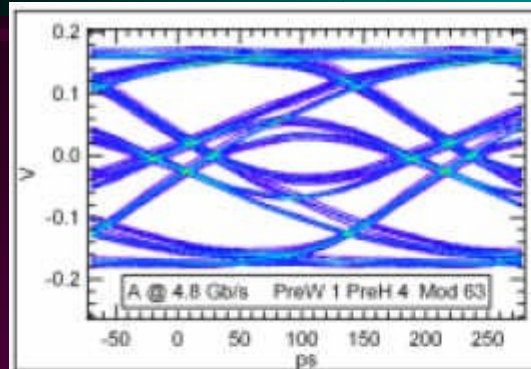
$$I_{MOD} = 0.142 \times M + 1.9 \text{ [mA]}$$

$$I_{BIAS} = 0.158 \times M + 1.8 \text{ [mA]}$$



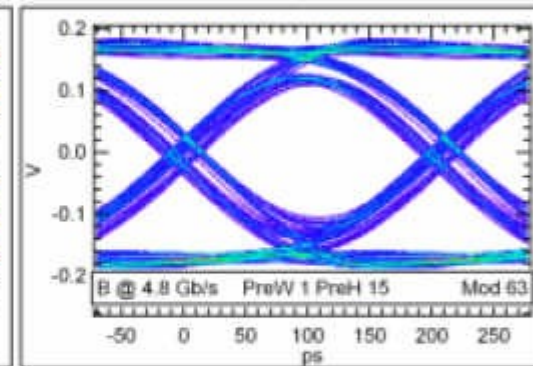
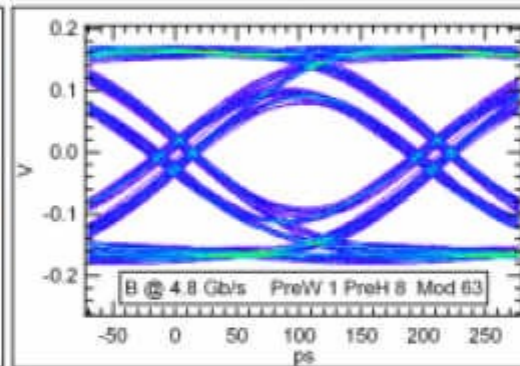
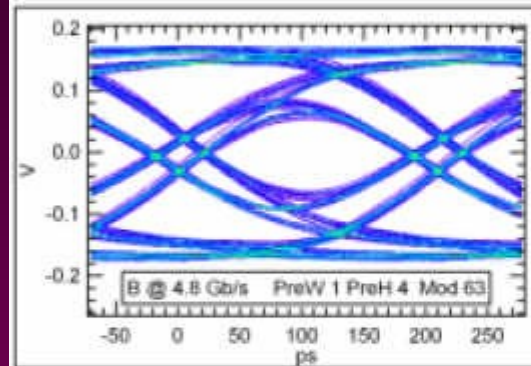
Tests with pre-emphasis

A



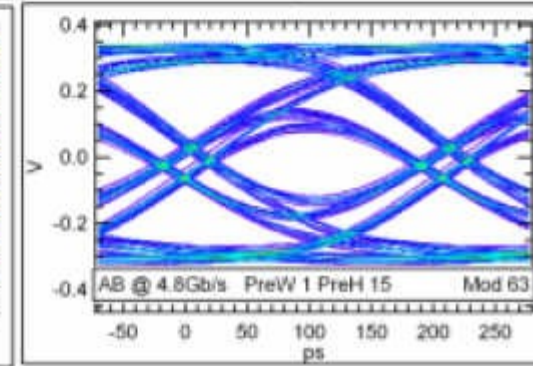
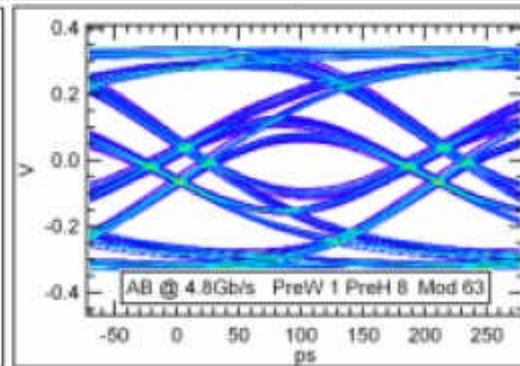
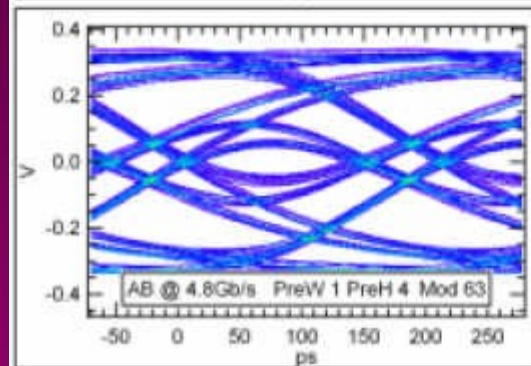
4.8 Gb/s

B



4.8 Gb/s

A+B

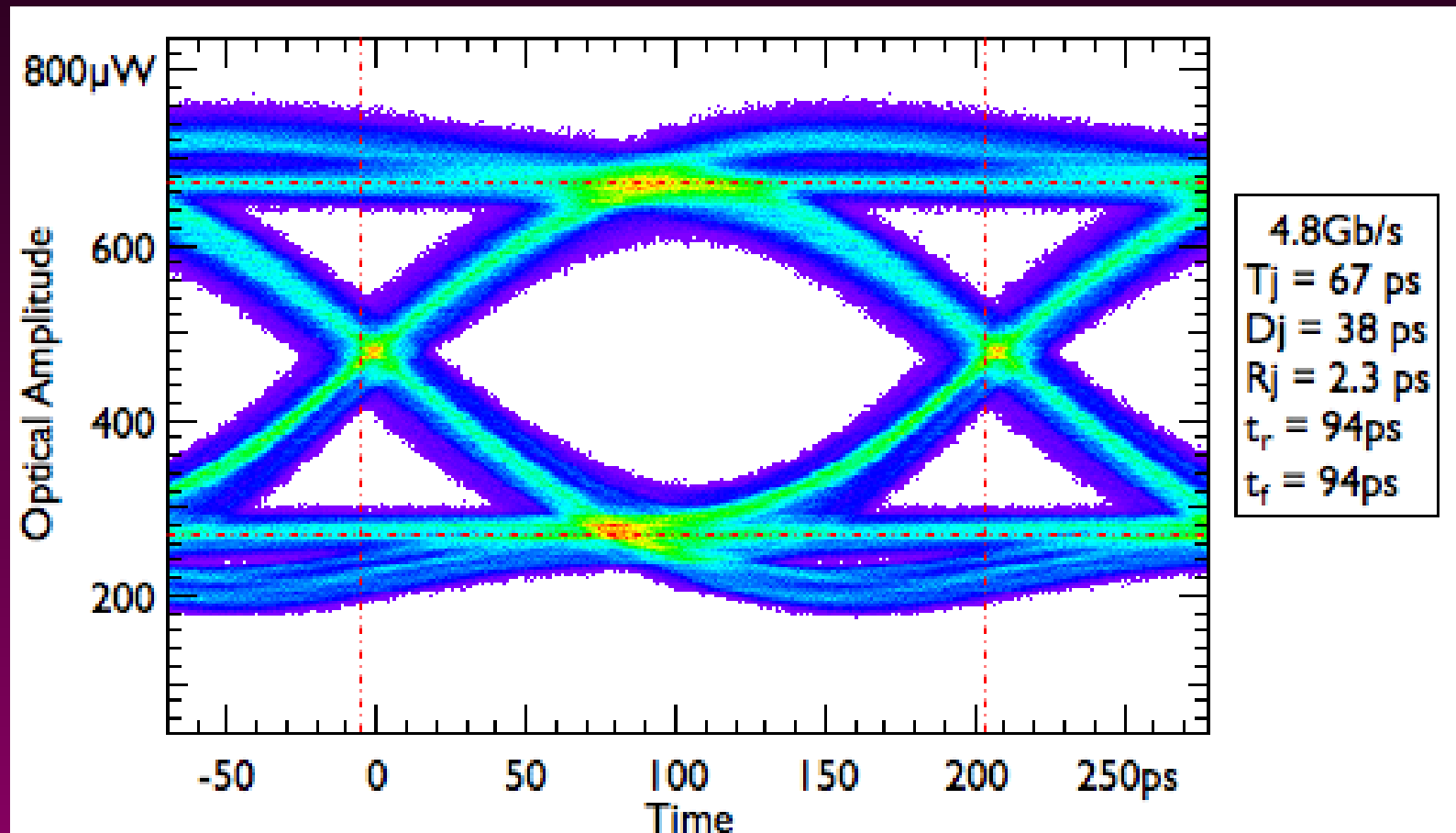


4.8 Gb/s

Test with VCSEL



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Conclusions



Sezione di Torino

- * A 5 Gb/s laser driver in CMOS 0.13 μm technology has been designed and tested.
- * The prototype is functional but does not have enough bandwidth - 5 Gb/s operation possible only with max pre-emphasis
- * Performances not yet acceptable...
...but not so far from specs.
- * Problems in parasitic capacitance evaluation and layout symmetry have been recognized.
- * A new version submission is planned for November 2009